

# Xu Yang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2595855/publications.pdf>

Version: 2024-02-01

9  
papers

218  
citations

1040056  
9  
h-index

1474206  
9  
g-index

9  
all docs

9  
docs citations

9  
times ranked

101  
citing authors

#	ARTICLE	IF	CITATIONS
1	Efficient and slurryless ultrasonic vibration assisted electrochemical mechanical polishing for 4H-SiC wafers. <i>Ceramics International</i> , 2022, 48, 7570-7583.	4.8	21
2	Dominant factors and their action mechanisms on material removal rate in electrochemical mechanical polishing of 4H-SiC (0001) surface. <i>Applied Surface Science</i> , 2021, 562, 150130.	6.1	17
3	Highly efficient planarization of sliced 4H-SiC (0001) wafer by slurryless electrochemical mechanical polishing. <i>International Journal of Machine Tools and Manufacture</i> , 2019, 144, 103431.	13.4	48
4	Etching Characteristics of Quartz Crystal Wafers Using Argon-Based Atmospheric Pressure CF <sub>4</sub> Plasma Stabilized by Ethanol Addition. <i>Nanomanufacturing and Metrology</i> , 2019, 2, 168-176.	3.0	13
5	Obtaining Atomically Smooth 4H-SiC (0001) Surface by Controlling Balance Between Anodizing and Polishing in Electrochemical Mechanical Polishing. <i>Nanomanufacturing and Metrology</i> , 2019, 2, 140-147.	3.0	27
6	Ultrasonic-assisted anodic oxidation of 4H-SiC (0001) surface. <i>Electrochemistry Communications</i> , 2019, 100, 1-5.	4.7	26
7	Surface Modification and Microstructuring of 4H-SiC(0001) by Anodic Oxidation with Sodium Chloride Aqueous Solution. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 2535-2542.	8.0	16
8	Investigation of anodic oxidation mechanism of 4H-SiC (0001) for electrochemical mechanical polishing. <i>Electrochimica Acta</i> , 2018, 271, 666-676.	5.2	39
9	Optimization of Gas Composition Used in Plasma Chemical Vaporization Machining for Figuring of Reaction-Sintered Silicon Carbide with Low Surface Roughness. <i>Scientific Reports</i> , 2018, 8, 2376.	3.3	11